

# PSMN2R8-40BS

# N-channel 40 V 2.9 m $\Omega$ standard level MOSFET in D2PAK Rev. 1 — 20 March 2012 Product data

Product data sheet

#### 1. **Product profile**

## 1.1 General description

Standard level N-channel MOSFET in SOT404 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

## 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

## 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	[1]	-	-	100	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	211	W
Tj	junction temperature			-55	-	175	°C
Static char	acteristics						
R <sub>DSon</sub> drain-source on-state	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 100 ^{\circ}\text{C};$ see <u>Figure 13</u> ; see <u>Figure 14</u>		-	3.58	4.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 14		-	2.47	2.9	mΩ
Dynamic c	haracteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; V_{DS} = 20 \text{ V};$		-	17	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 15; see Figure 16		-	71	-	nC
Avalanche	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 40 V; unclamped; $R_{GS}$ = 50 $\Omega$		-	-	407	mJ

<sup>[1]</sup> Continuous current rating is limited by package.



## 2. Pinning information

Table 2. Pinning information

I do L.		illioniation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb D	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make connection to pin 2

## 3. Ordering information

Table 3. Ordering information

Type number Package			
	Name	Description	Version
PSMN2R8-40BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN2R8-40BS	PSMN2R8-40BS

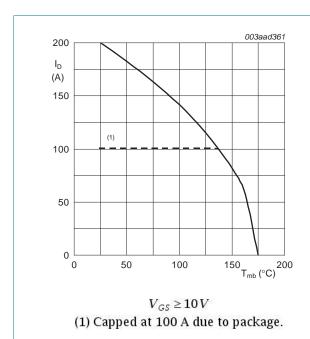
## **Limiting values**

Table 5. **Limiting values** 

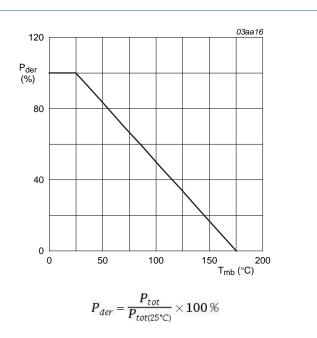
In accordance with the Absolute Maximum Rating System (IEC 60134).

		, ,				
Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
$V_{DGR}$	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	40	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	100	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$	<u>[1]</u>	-	100	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25  ^{\circ}C$ ; see Figure 3		-	797	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	211	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-dr	ain diode					
Is	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u>	-	100	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	797	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 100 A; $V_{sup} \le$ 40 V; unclamped; $R_{GS}$ = 50 $\Omega$		-	407	mJ

[1] Continuous current rating is limited by package.



Continuous drain current as a function of mounting base temperature



Normalized total power dissipation as a function of mounting base temperature

PSMN2R8-40BS

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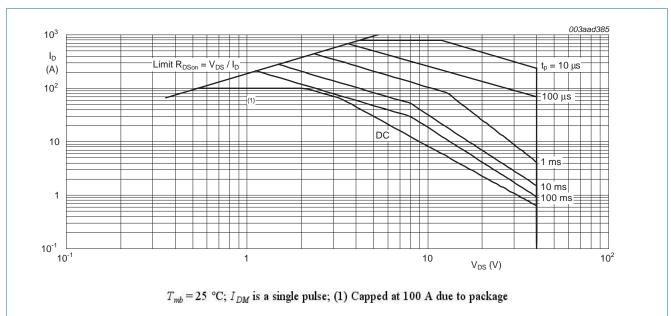


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.4	0.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	50	-	K/W

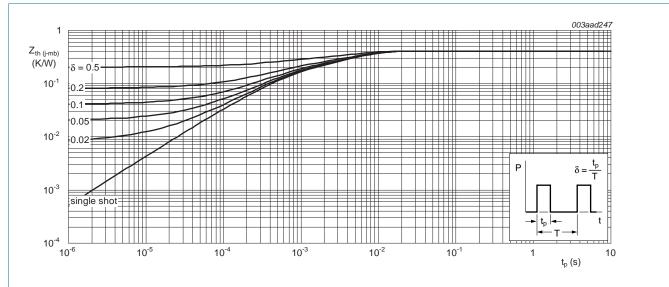


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 7. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	-	-	4.6	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; see <u>Figure 10</u> ; see <u>Figure 12</u>	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2.3	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	10	μΑ
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	150	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nΑ
R <sub>DSon</sub> drain-source on-state resistance	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 100 °C; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	3.58	4.2	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 10 A; $T_j$ = 175 °C; see Figure 13; see Figure 14	-	4.94	5.8	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A}; T_j = 25 \text{ °C};$ see Figure 14	-	2.47	2.9	mΩ	
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.7	-	Ω
Dynamic c	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	61	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 10 \text{ V}; \text{see}$	-	71	-	nC
Q <sub>GS</sub>	gate-source charge	Figure 15; see Figure 16	-	21	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	13	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	8.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	17	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 10 \text{ A}$ ; $V_{DS} = 20 \text{ V}$ ; see <u>Figure 15</u> ; see <u>Figure 16</u>	-	4.7	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4491	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	937	-	рF
C <sub>rss</sub>	reverse transfer capacitance		-	464	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 10 \text{ V};$	-	28	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	29	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	52	-	ns
t <sub>f</sub>	fall time		-	23	-	ns

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 Table 7.
 Characteristics ...continued

Tested to JEDEC standards where applicable.

	•					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 18</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 10 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 20 \text{ V}$	-	47	-	ns
Q <sub>r</sub>	recovered charge	$I_S = 10 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{GS} = 0 \text{ V; } V_{DS} = 20 \text{ V; } T_j = 25 \text{ °C}$	-	61	-	nC

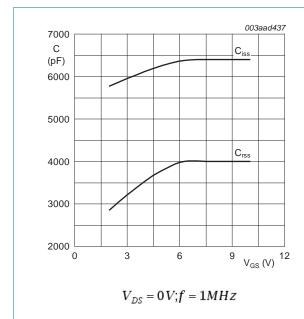


Fig 5. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

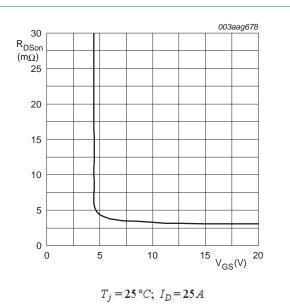
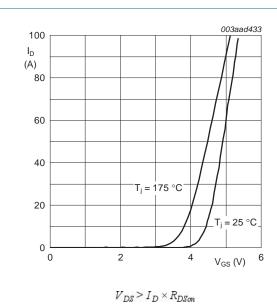
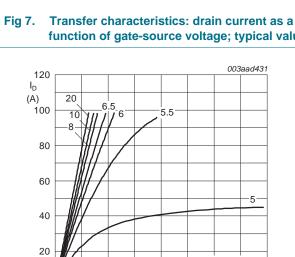


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C$ 

0.3

0

Fig 9. Output characteristics: drain current as a function of drain-source voltage; typical values

0.6

 $V_{GS}(V) = 4.5$ 

0.9 <sub>VDS</sub> (V) 1.2

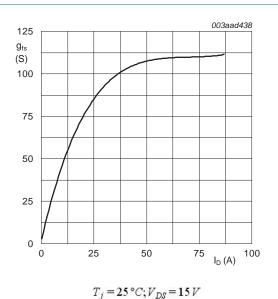
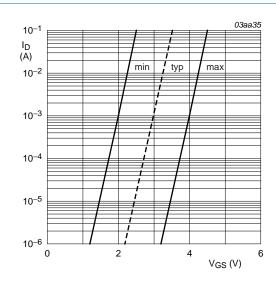


Fig 8. Forward transconductance as a function of drain current; typical values



 $T_j=25\,^{\circ}C; V_{DS}=5V$ 

Fig 10. Sub-threshold drain current as a function of gate-source voltage

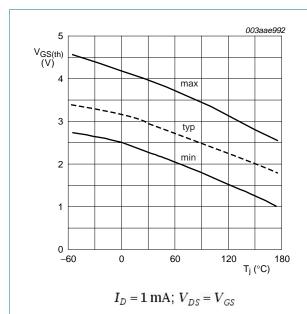


Fig 11. Gate-source threshold voltage as a function of junction temperature

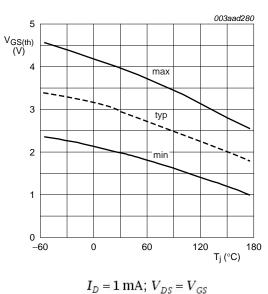


Fig 12. Gate-source threshold voltage as a function of junction temperature

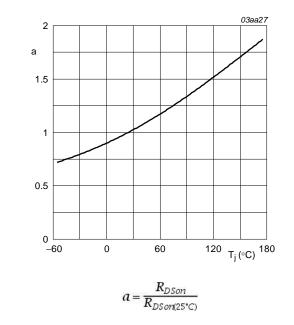


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

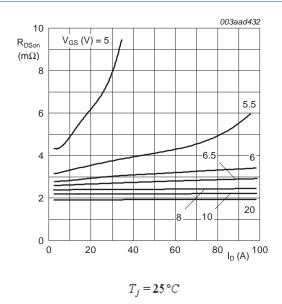
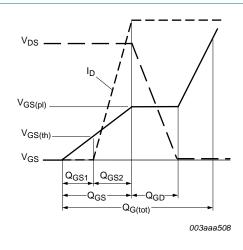


Fig 14. Drain-source on-state resistance as a function of drain current; typical values

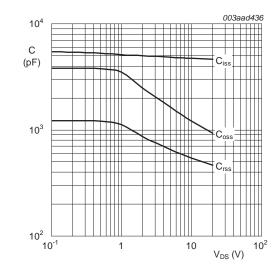


10 003aad435 (V) 8 V V<sub>DS</sub> = 20 V 40 60 Q<sub>G</sub> (nC) 80

 $T_j = 25 \,^{\circ}C; I_D = 10A$ 

Fig 15. Gate charge waveform definitions





 $V_{GS} = 0V; f = 1MHz$ 

Fig 17. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

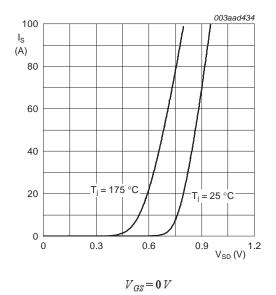


Fig 18. Source current as a function of source-drain voltage; typical values

## 8. Package outline

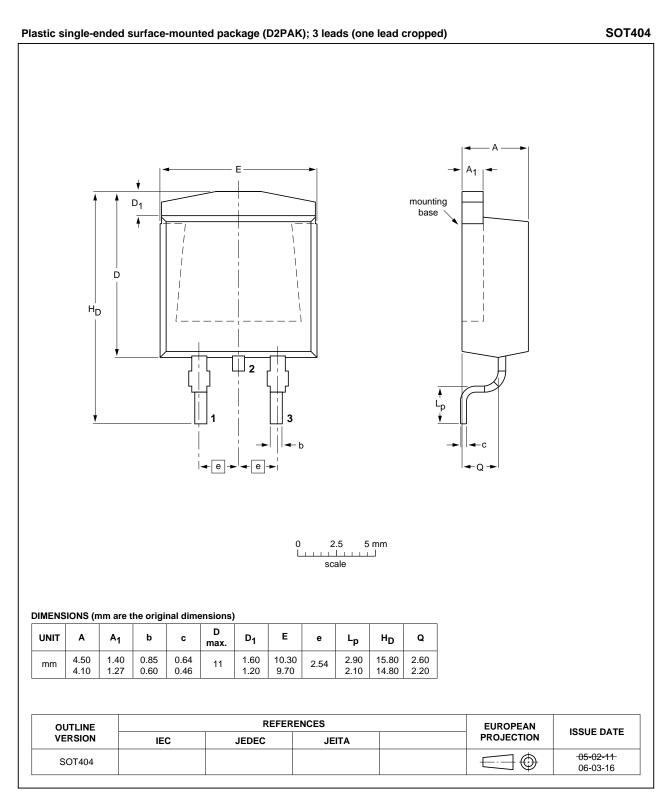


Fig 19. Package outline SOT404 (D2PAK)

# 9. Revision history

## Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN2R8-40BS v.1	20120320	Product data sheet	-	-

## 10. Legal information

#### 10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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## PSMN2R8-40BS

#### N-channel 40 V 2.9 mΩ standard level MOSFET in D2PAK

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# PSMN2R8-40BS

## **Nexperia**

## N-channel 40 V 2.9 m $\Omega$ standard level MOSFET in D2PAK

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